

2N4403

Preferred Device

General Purpose Transistors

PNP Silicon

Features

- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CE0}	40	Vdc
Collector – Base Voltage	V_{CBO}	40	Vdc
Emitter – Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	600	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

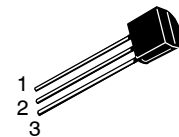
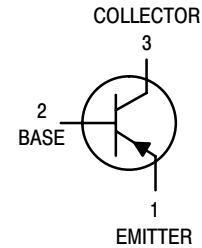
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$



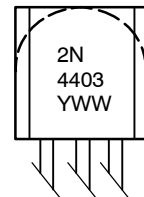
ON Semiconductor®

<http://onsemi.com>



TO-92
CASE 29
STYLE 1

MARKING DIAGRAM



Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 78 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (Note 4) (I _C = 1.0 mA _{dc} , I _B = 0)	V _{(BR)CEO}	40	–	V _{dc}	
Collector–Base Breakdown Voltage (I _C = 0.1 mA _{dc} , I _E = 0)	V _{(BR)CBO}	40	–	V _{dc}	
Emitter–Base Breakdown Voltage (I _E = 0.1 mA _{dc} , I _C = 0)	V _{(BR)EBO}	5.0	–	V _{dc}	
Base Cutoff Current (V _{CE} = 35 V _{dc} , V _{EB} = 0.4 V _{dc})	I _{BEV}	–	0.1	μA _{dc}	
Collector Cutoff Current (V _{CE} = 35 V _{dc} , V _{EB} = 0.4 V _{dc})	I _{CEX}	–	0.1	μA _{dc}	
ON CHARACTERISTICS					
DC Current Gain (I _C = 0.1 mA _{dc} , V _{CE} = 1.0 V _{dc}) (I _C = 1.0 mA _{dc} , V _{CE} = 1.0 V _{dc}) (I _C = 10 mA _{dc} , V _{CE} = 1.0 V _{dc}) (I _C = 150 mA _{dc} , V _{CE} = 2.0 V _{dc}) (Note 4) (I _C = 500 mA _{dc} , V _{CE} = 2.0 V _{dc}) (Note 4)	h _{FE}	30 60 100 100 20	– – – 300 –	–	
Collector–Emitter Saturation Voltage (Note 4) (I _C = 150 mA _{dc} , I _B = 15 mA _{dc}) (I _C = 500 mA _{dc} , I _B = 50 mA _{dc})	V _{CE(sat)}	– –	0.4 0.75	V _{dc}	
Base–Emitter Saturation Voltage (Note 4) (I _C = 150 mA _{dc} , I _B = 15 mA _{dc}) (I _C = 500 mA _{dc} , I _B = 50 mA _{dc})	V _{BE(sat)}	0.75 –	0.95 1.3	V _{dc}	
SMALL–SIGNAL CHARACTERISTICS					
Current–Gain – Bandwidth Product (I _C = 20 mA _{dc} , V _{CE} = 10 V _{dc} , f = 100 MHz)	f _T	200	–	MHz	
Collector–Base Capacitance (V _{CB} = 10 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{cb}	–	8.5	pF	
Emitter–Base Capacitance (V _{EB} = 0.5 V _{dc} , I _C = 0, f = 1.0 MHz)	C _{eb}	–	30	pF	
Input Impedance (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz)	h _{ie}	1.5 k	15 k	ohms	
Voltage Feedback Ratio (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz)	h _{re}	0.1	8.0	X 10 ^{–4}	
Small–Signal Current Gain (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz)	h _{fe}	60	500	–	
Output Admittance (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz)	h _{oe}	1.0	100	μmhos	
SWITCHING CHARACTERISTICS					
Delay Time	(V _{CC} = 30 V _{dc} , V _{BE} = +2.0 V _{dc} , I _C = 150 mA _{dc} , I _{B1} = 15 mA _{dc})	t _d	–	15	ns
Rise Time		t _r	–	20	ns
Storage Time	(V _{CC} = 30 V _{dc} , I _C = 150 mA _{dc} , I _{B1} = 15 mA, I _{B2} = 15 mA)	t _s	–	225	ns
Fall Time		t _f	–	30	ns

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

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ORDERING INFORMATION

Device	Package	Shipping†
2N4403	TO-92	5,000 Units / Box
2N4403G	TO-92 (Pb-Free)	5,000 Units / Box
2N4403RL	TO-92	2,000 / Tape & Reel
2N4403RLRA	TO-92	2,000 / Tape & Reel
2N4403RLRAG	TO-92 (Pb-Free)	2,000 / Tape & Reel
2N4403RLRM	TO-92	2,000 / Ammo Pack
2N4403RLRP	TO-92	2,000 / Ammo Pack
2N4403RLRPG	TO-92 (Pb-Free)	2,000 / Ammo Pack
2N4403ZL1	TO-92	2,000 / Ammo Pack

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

SWITCHING TIME EQUIVALENT TEST CIRCUIT

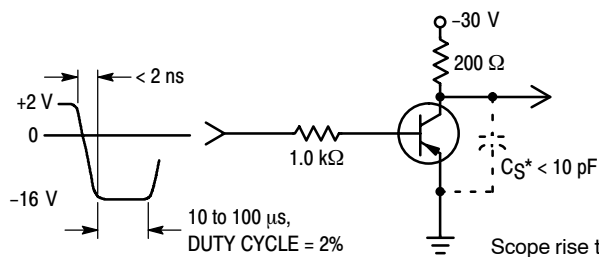


Figure 1. Turn-On Time

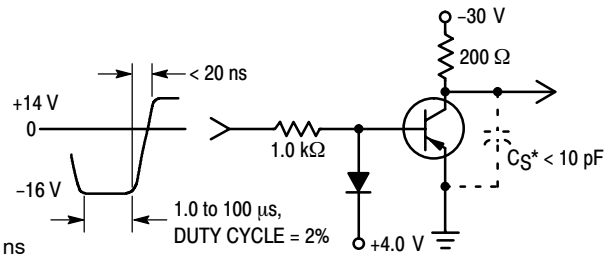


Figure 2. Turn-Off Time

TRANSIENT CHARACTERISTICS

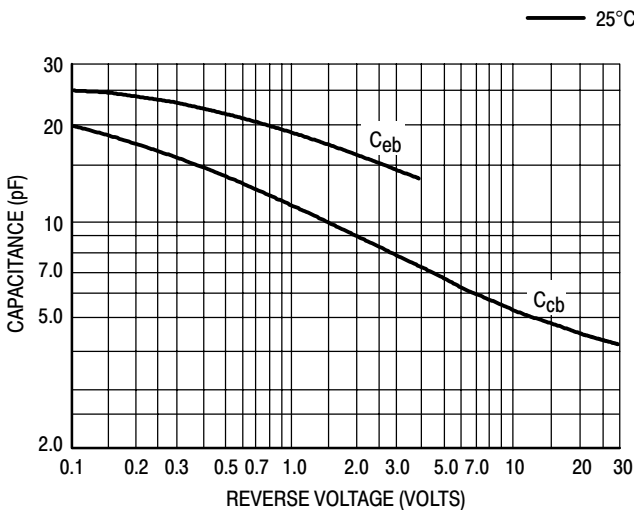


Figure 3. Capacitances

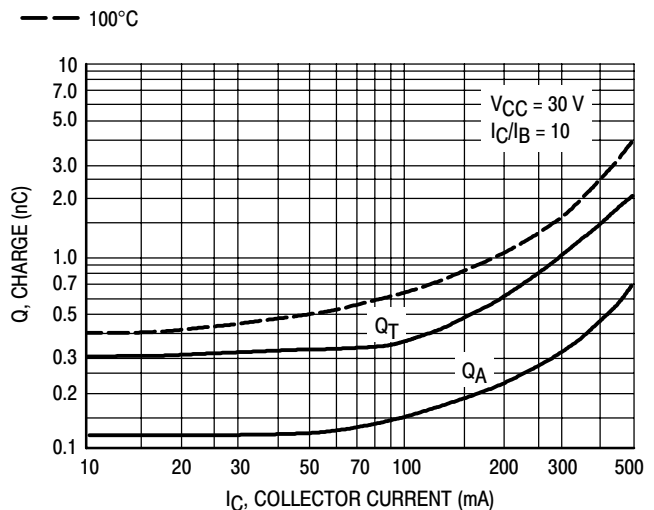


Figure 4. Charge Data

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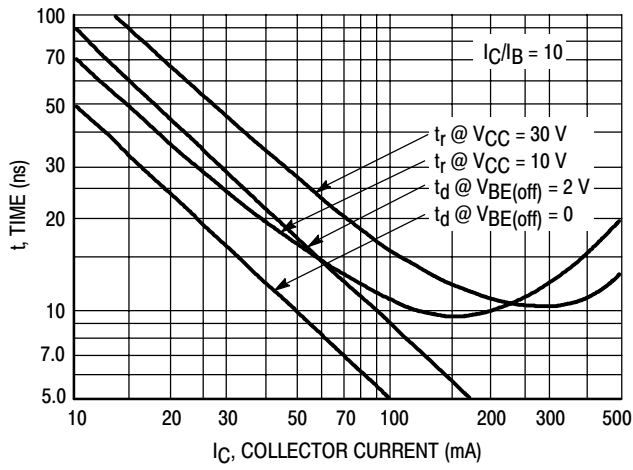


Figure 5. Turn-On Time

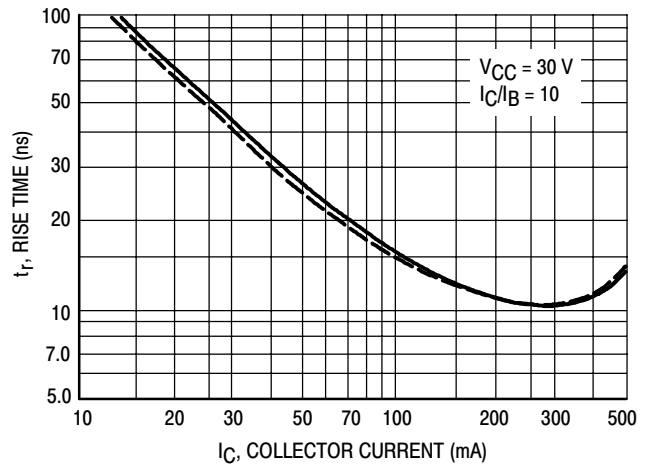


Figure 6. Rise Time

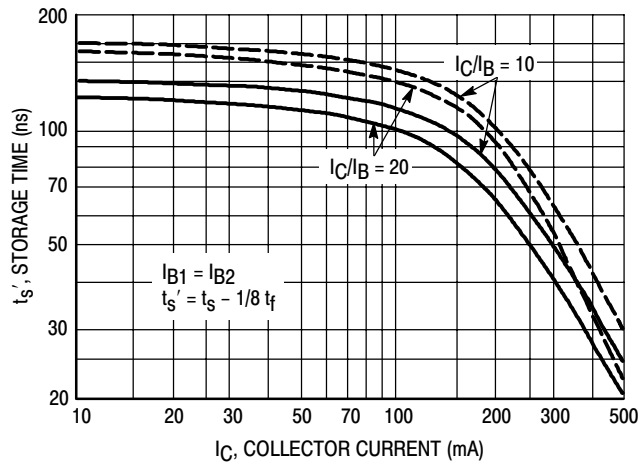


Figure 7. Storage Time

SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

$V_{CE} = -10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$; Bandwidth = 1.0 Hz

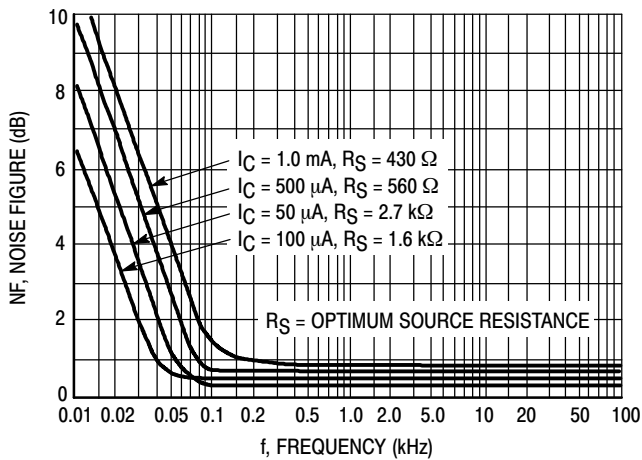


Figure 8. Frequency Effects

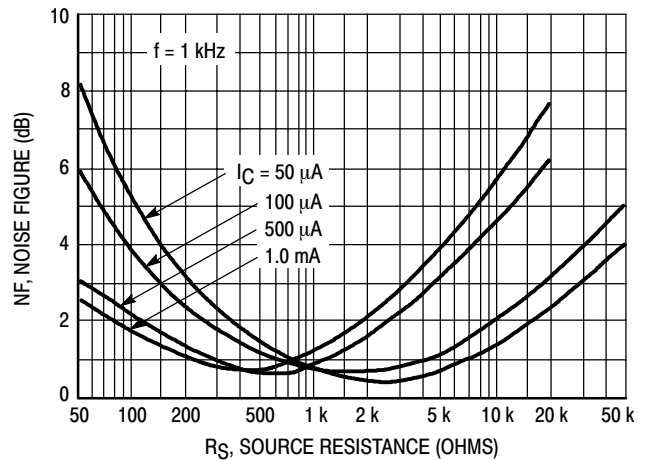


Figure 9. Source Resistance Effects

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h PARAMETERS

$V_{CE} = -10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$, $T_A = 25^\circ\text{C}$

This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were

selected from the 2N4403 lines, and the same units were used to develop the correspondingly-numbered curves on each graph.

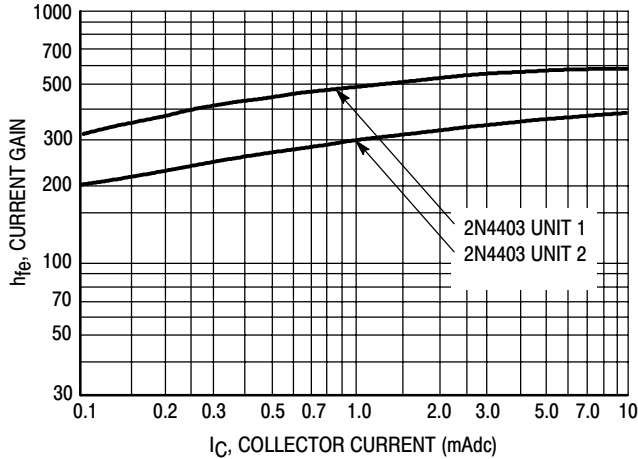


Figure 10. Current Gain

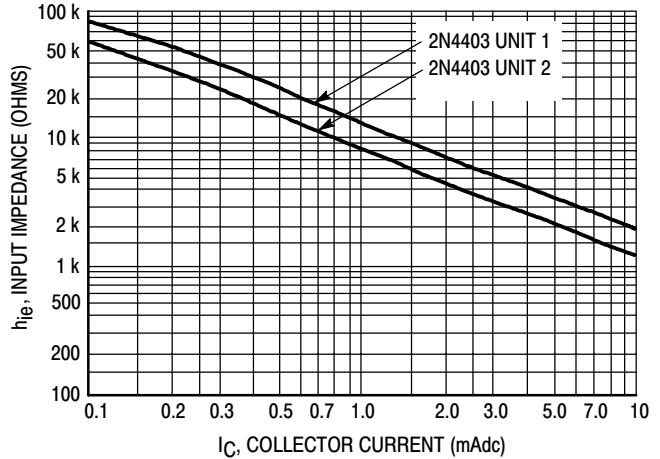


Figure 11. Input Impedance

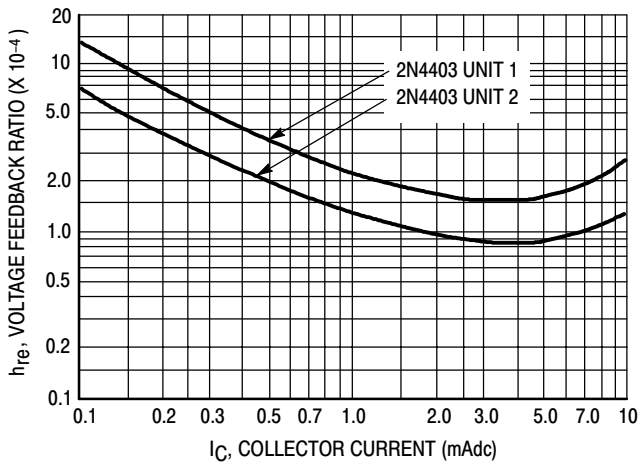


Figure 12. Voltage Feedback Ratio

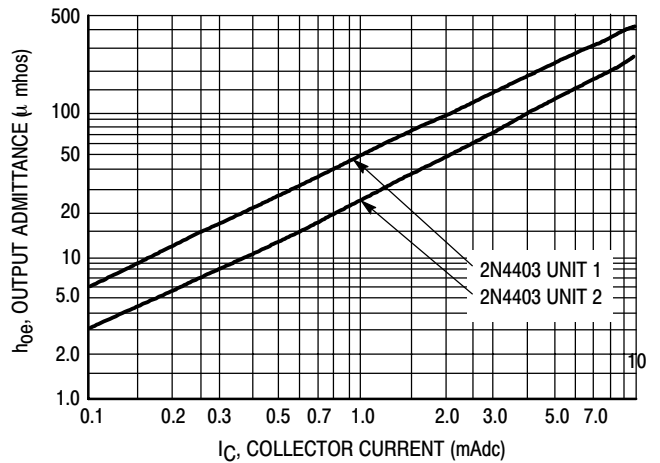


Figure 13. Output Admittance

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STATIC CHARACTERISTICS

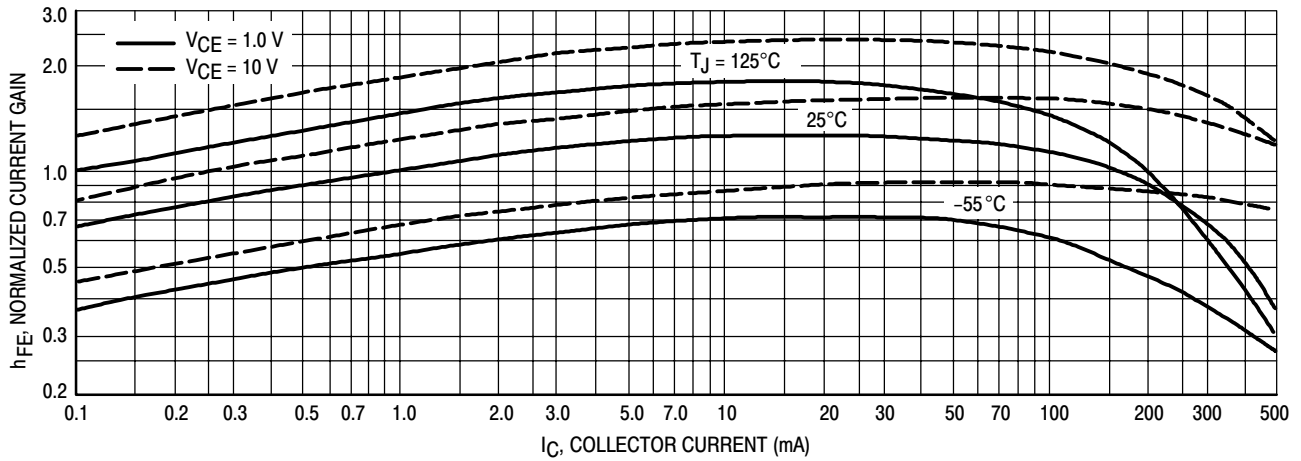


Figure 14. DC Current Gain

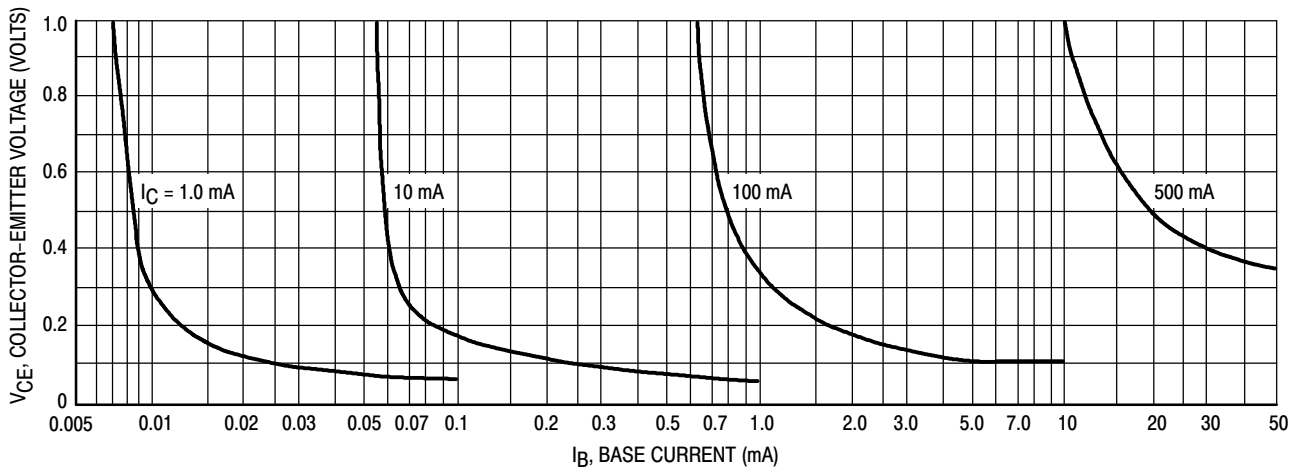


Figure 15. Collector Saturation Region

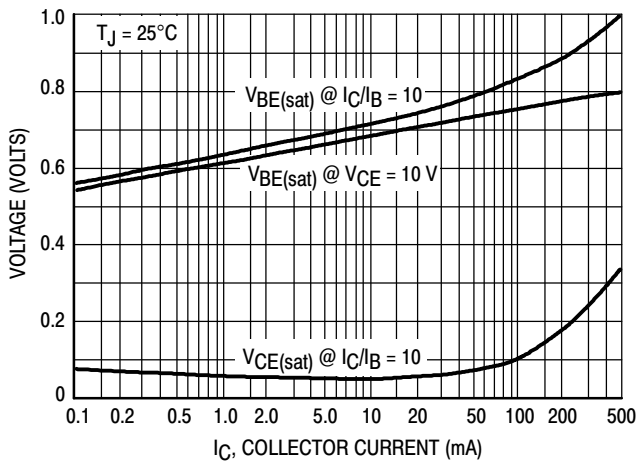


Figure 16. "On" Voltages

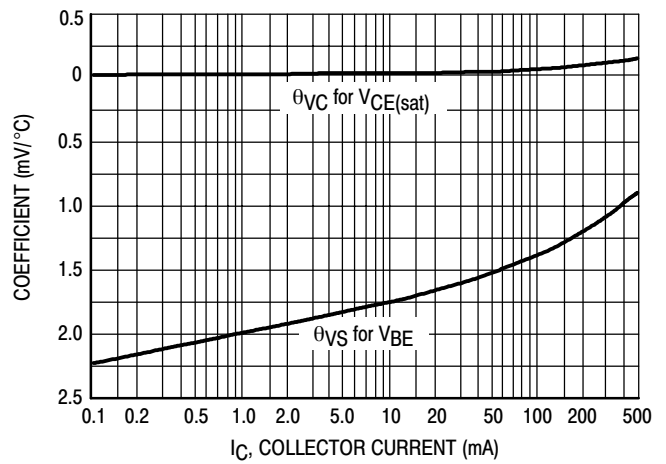


Figure 17. Temperature Coefficients